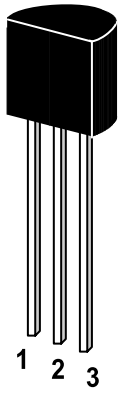
ST 2SC2785

NPN Silicon Epitaxial Planar Transistor
for switching and AF amplifier applications.

The transistor is subdivided into four groups, O, Y, G and L, according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base

TO-92 Plastic Package
Weight approx. 0.19g

Absolute Maximum Ratings (T_a = 25℃)

	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	60	V
Collector Emitter Voltage	V_{CEO}	50	V
Emitter Base Voltage	V_{EBO}	5	V
Collector Current	I_C	150	mA
Power Dissipation	P_{tot}	250	mW
Junction Temperature	T_j	150	^{O}C
Storage Temperature Range	T_S	-55 to +150	^{O}C

SEMTECH ELECTRONICS LTD.
(Subsidiary of Sino-Tech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)

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Characteristics at T_{amb}=25 °C

	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain					
at V_{CE}=6V, I_C=1mA					
Current Gain Group O	h_{FE}	70	-	140	-
Y	h_{FE}	120	-	240	-
G	h_{FE}	200	-	400	-
L	h_{FE}	350	-	700	-
Collector Base Breakdown Voltage					
at I_C=100μA	$V_{(BR)CBO}$	60	-	-	V
Collector Emitter Breakdown Voltage					
at I_C=10mA	$V_{(BR)CEO}$	50	-	-	V
Emitter Base Breakdown Voltage					
at I_E=10μA	$V_{(BR)EBO}$	5	-	-	V
Collector Cutoff Current					
at V_{CB}=40V	I_{CBO}	-	-	0.1	μA
Emitter Cutoff Current					
at V_{EB}=3V	I_{EBO}	-	-	0.1	μA
Collector Saturation Voltage					
at I_C=100mA, I_B=10mA	$V_{CE(sat)}$	-	0.15	0.3	V
Gain Bandwidth Product					
at V_{CE}=6V, I_C=10mA	f_T	-	300	-	MHz
Output Capacitance					
at V_{CB}=6V, f=1MHz	C_{OB}	-	2.5	-	pF
Noise Figure					
at V_{CE}=6V, I_E=0.5mA					
f=1KHz, R_S=500Ω	NF	-	4	-	dB